

Supporting Information for

Enhancing electronic and optical properties of monolayer MoSe₂ via MoSe₂/Blue phosphorene heterobilayer

Huabing Shu,^{*a} Ying Wang^a and Minglei Sun^b

^aSchool of Science, Jiangsu University of Science and Technology, Zhenjiang 212001, China

^bSchool of Mechanical Engineering, Southeast University, Nanjing, 211189, China

*E-mail: shuhuabing@just.edu.cn

Table S1 Calculated structural parameters and bandgaps of the monolayers and heterobilayers: lattice constants (a/b), bond lengths (l), interlayer distances (d), formation energies (E_f), and bandgaps at DFT-PBE (E_{g-PBE}) and G_0W_0 ($E_{g-G_0W_0}$) levels. “dir” and “ind” represent the direct and indirect of bandgap, respectively.

Name	a/b (Å)	l_{P-P} (Å)	l_{Mo-Se} (Å)	d (Å)	E_f (meV/unit)	E_{g-PBE} (eV)	$E_{g-G_0W_0}$ (eV)
MoSe ₂	3.322	—	2.549	—	—	1.44 ^{dir}	2.30 ^{dir}
Blue-P	3.269	2.271	—	—	—	1.92 ^{ind}	3.35 ^{ind}
AA-stacking	3.291	2.270	2.535	3.697	-211.9	1.15 ^{ind}	1.63 ^{ind}
AB _{Mo} -stacking	3.294	2.270	2.537	3.852	-185.4	1.12 ^{ind}	1.59 ^{ind}
AB _{Se} -stacking	3.288	2.269	2.535	3.809	-190.7	1.12 ^{ind}	1.58 ^{ind}

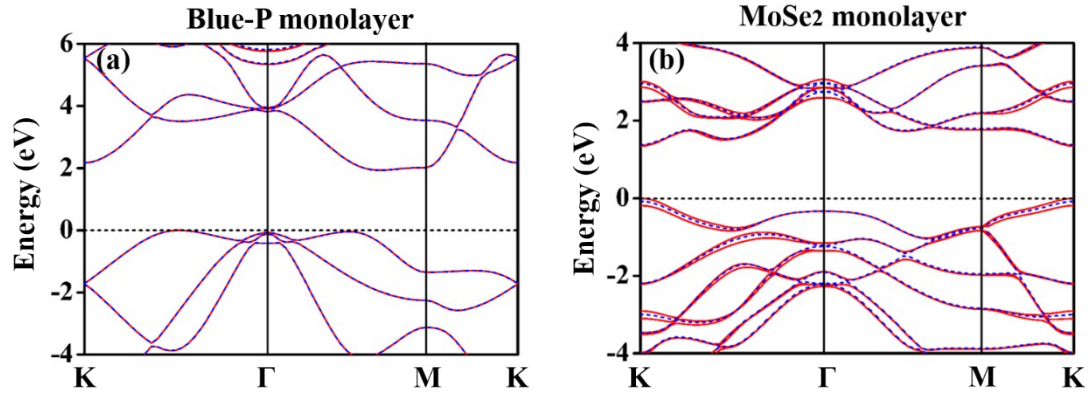


Fig. S1 Calculated band structures of monolayers with (red solid line) and without (blue dashed line) the spin-orbit coupling included at the DFT-PBE level: (a) Blue-P, (b) MoSe₂. The VBM is shifted to zero.

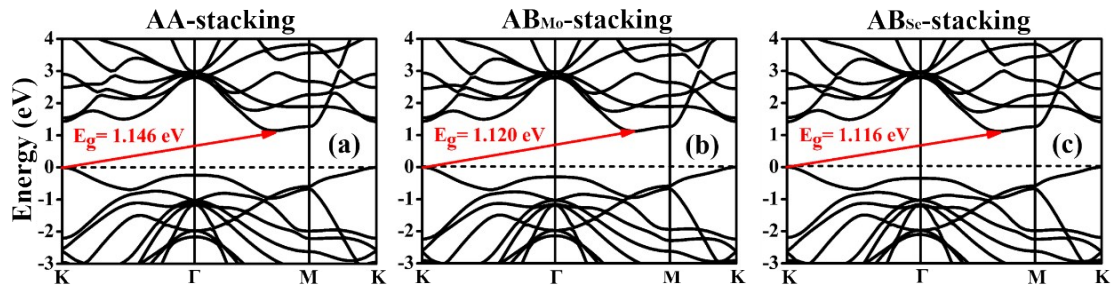


Fig. S2 Calculated band structures of MoSe₂/Blue-P heterobilayer at the DFT-PBE level: (a) AA-stacking, (b) AB_{Mo}-stacking, and (c) AB_{Se}-stacking. The VBM is shifted to zero.

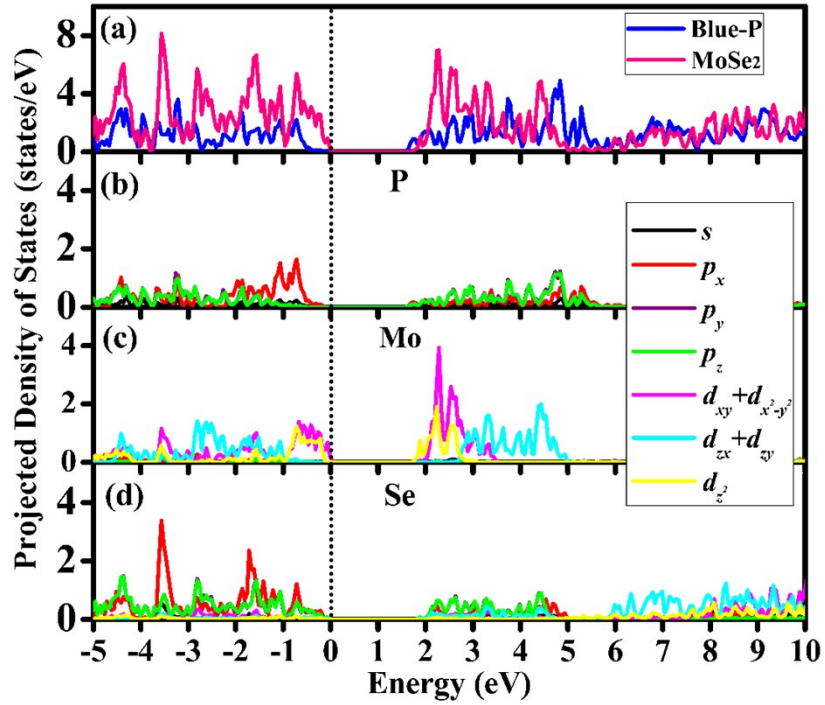


Fig. S3 (a), (b), (c) Projected density of states of the MoSe₂/Blue-P heterobilayer.

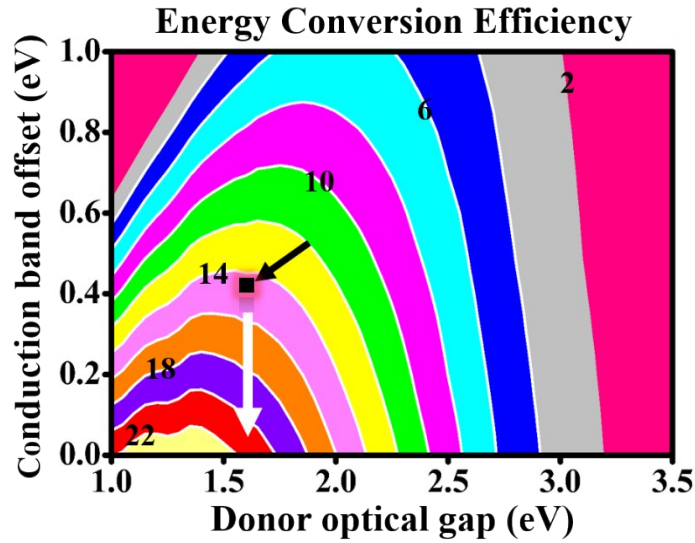


Fig. S4 Calculated energy-conversion efficiency contour as a function of the donor optical gap (MoSe₂ layer) and conduction band offset in MoSe₂/Blue-P heterobilayer. The white arrow indicates the trend of increase of energy-conversion efficiency through reducing the conduction band offset.